



# Vertical Cavity Surface Emitting Terahertz Lasers

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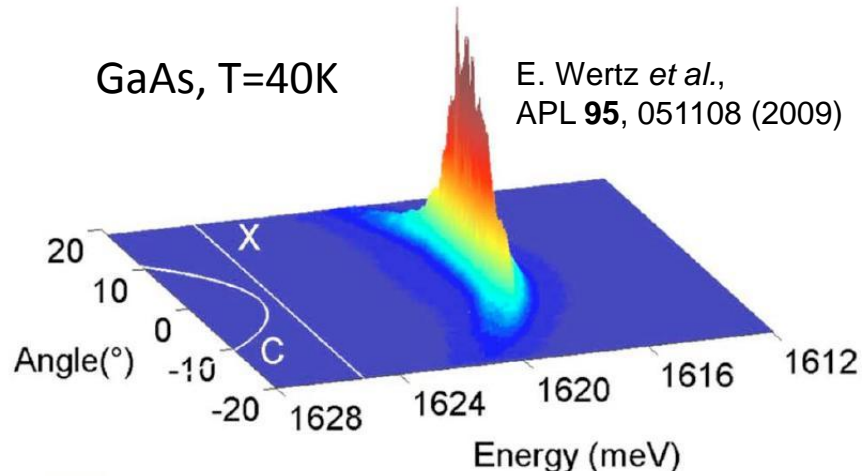
Mikhail Glazov (Ioffe Physico-Technical Institute)



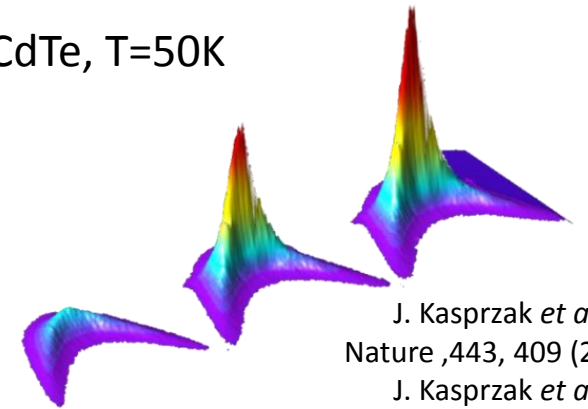
# Polariton Lasers

GaAs, T=40K

E. Wertz *et al.*,  
APL **95**, 051108 (2009)

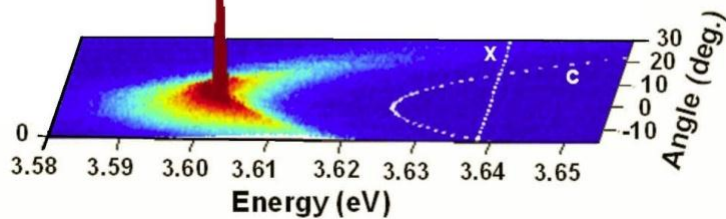


CdTe, T=50K



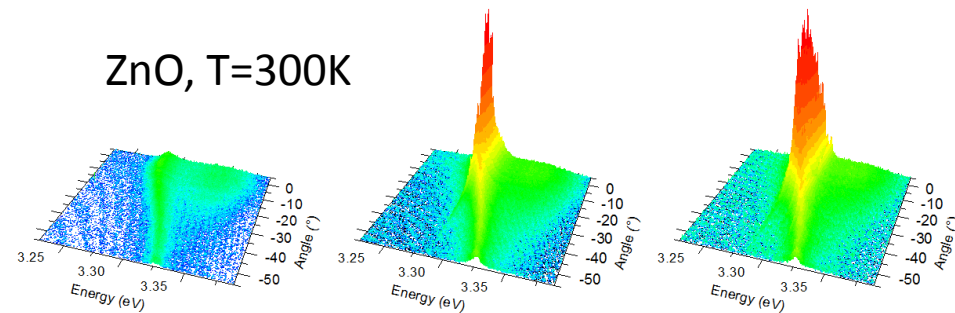
J. Kasprzak *et al.*  
Nature ,443, 409 (2006)  
J. Kasprzak *et al.*  
PRL ,101, 146404 (2008)

GaN, T=300K



G. Christmann *et al.*,  
APL **93**, 051102 (2008)

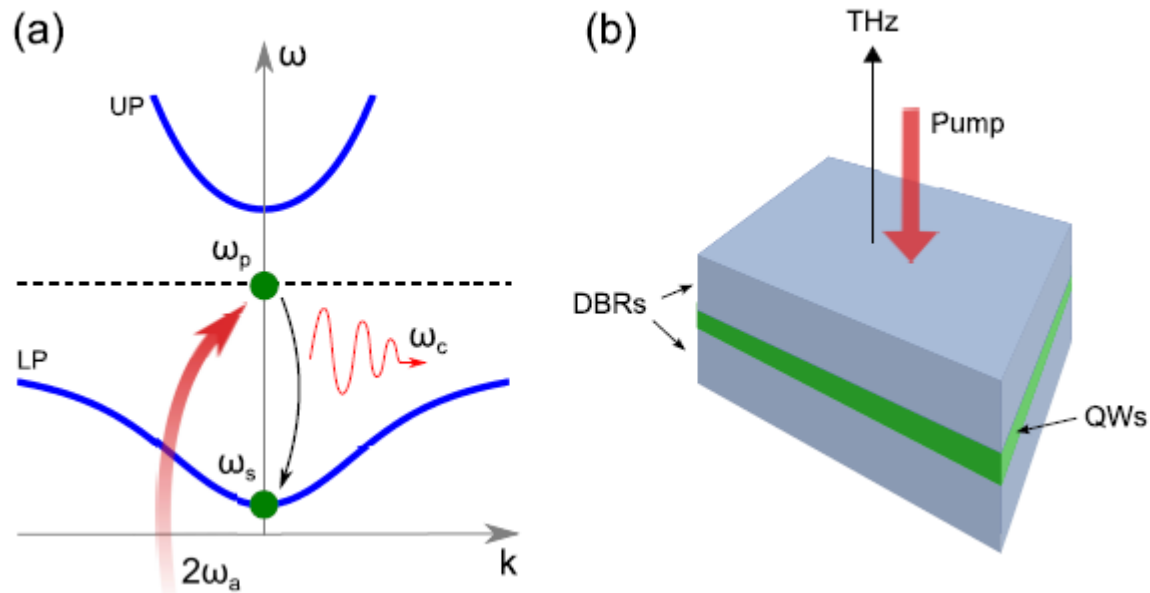
ZnO, T=300K



Thierry Guillet, this conference



## Vertical Cavity Surface Emitting Terahertz Lasers based on Polariton Lasers



- Excitation of a 2p exciton state by a two-photon absorption
- 1s polariton state populated due to the THz transition from 2p state
- Polariton population of 1s state stimulates the THz transition
- Per each visible photon the device emits a THz photon
- Vertical geometry! No terahertz cavity needed!



# 2p-exciton state

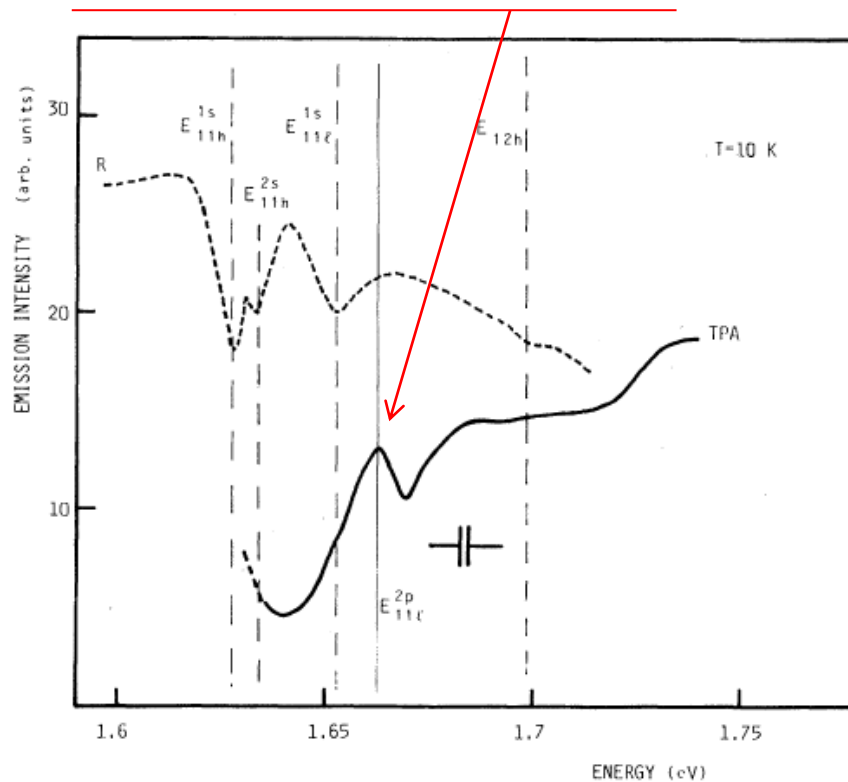


FIG. 1. Two-photon absorption luminescence excitation spectrum of sample *A* vs  $2\hbar\omega$  at 10 K (TPA curve).

## Two-photon spectroscopy in GaAs/Al<sub>x</sub>Ga<sub>1-x</sub>As multiple quantum wells

I. M. Catalano, A. Cingolani, R. Cingolani, and M. Lepore  
*Dipartimento di Fisica, Università degli Studi di Bari, via Amendola 173, 70126 Bari, Italy*

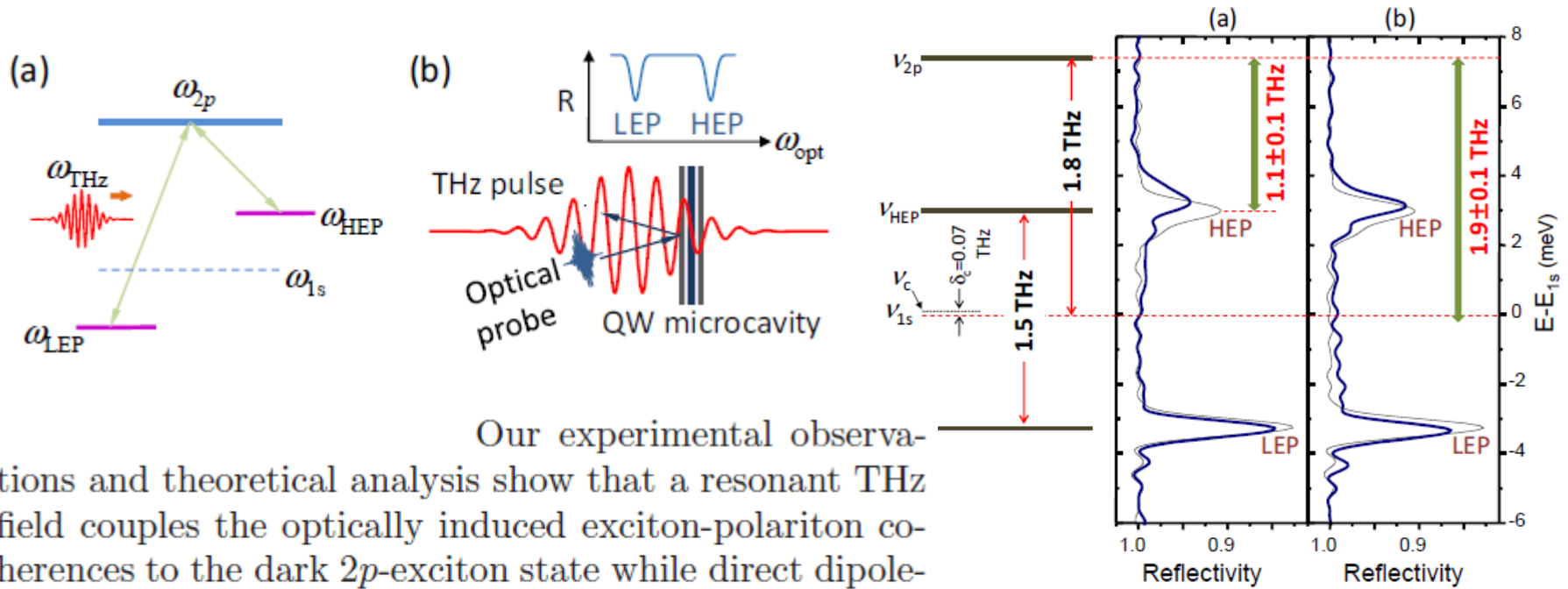
K. Ploog

*Max-Planck-Institut für Festkörperforschung, Heisenbergstrasse 1, D-7000 Stuttgart 80, Federal Republic of Germany*

(Received 18 January 1989)

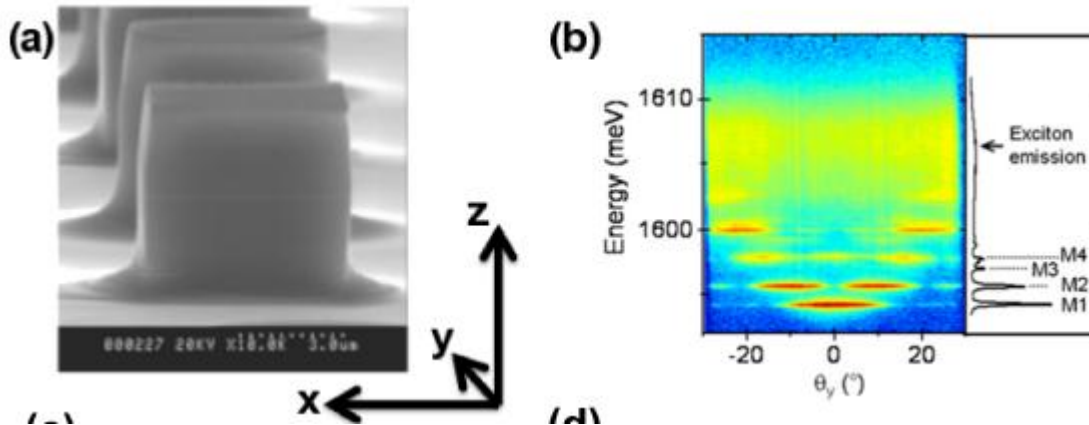


# 1s – 2p terahertz transition in a microcavity

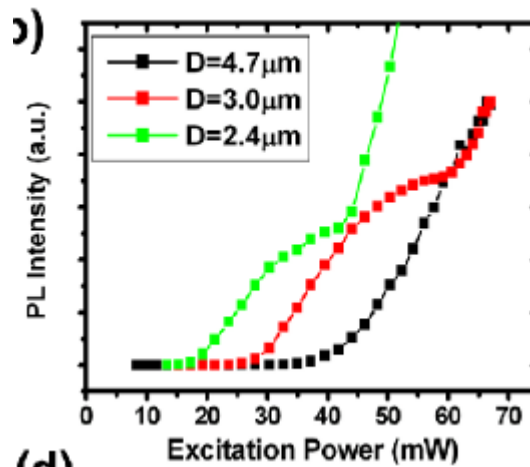




# Coherent injection of microcavity polaritons through two-photon absorption



Polariton lasing with a two-photon pump in a pillar GaAs microcavity



Courtesy of Alberto Bramati,  
Elisabeth Giacobino, LKB, Paris





# Theoretical treatment

$$\frac{d\rho}{dt} = \frac{i}{\hbar} [\rho, H_c] + \hat{L}\rho; \quad \text{Liouville equation for the density matrix}$$

$$\frac{dN_p}{dt} = \text{Tr} \left\{ p^+ p \frac{d\rho}{dt} \right\} = \frac{2}{\hbar\zeta} \text{Re} \{ \text{Tr} (\rho [H^-; [p^+ p; H^+]]) \} \quad \text{Master equation}$$

Rate equations:

$$\frac{dN_p}{dt} = -\frac{N_p}{\tau_p} + W_g \left[ \frac{g^{(2)}(0)}{2} N_a^2 - N_p (2N_a + 1) \right] + \quad \text{2p-population}$$

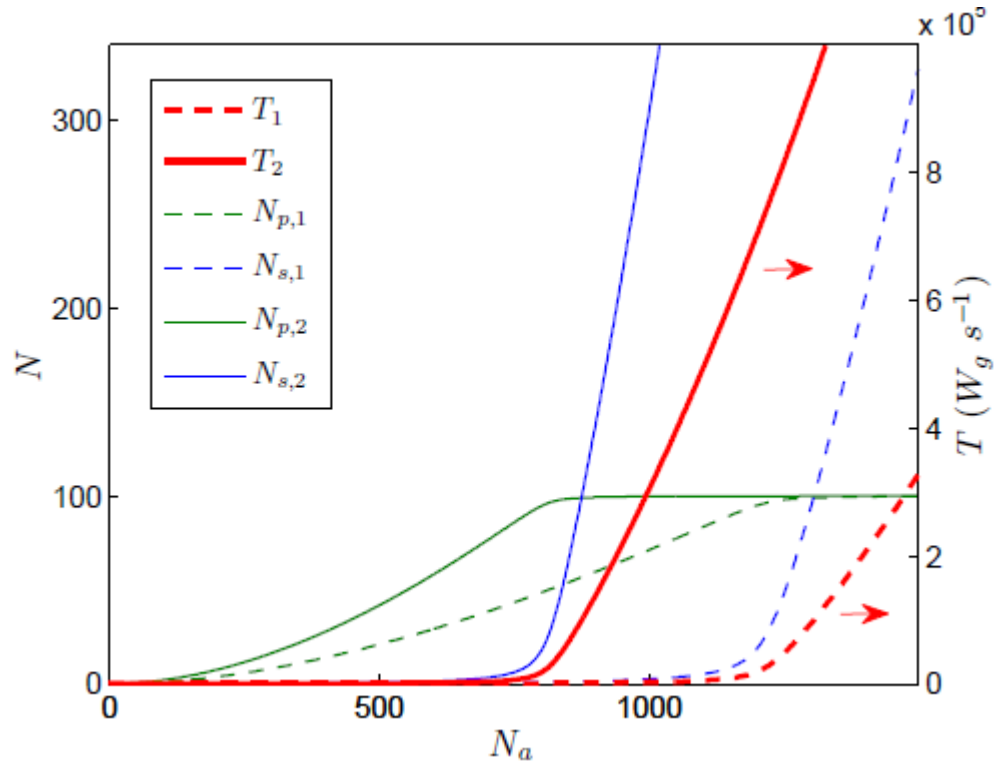
Second order coherence of pumping light

$$\frac{dN_s}{dt} = -\frac{N_s}{\tau_s} - \quad \text{1s-population}$$
$$-W_G \{ N_s N_c (N_p + 1) - N_p (N_s + 1) (N_c + 1) \},$$

$$\frac{dN_c}{dt} = -\frac{N_c}{\tau_c} - \quad \text{Terahertz population}$$
$$-W_G \{ N_s N_c (N_p + 1) - N_p (N_s + 1) (N_c + 1) \},$$



## Terahertz VCSEL: results of simulation



- Terahertz emission rate increases at the onset of polariton lasing
- 2p population saturates
- 1s population increases exponentially at lasing threshold

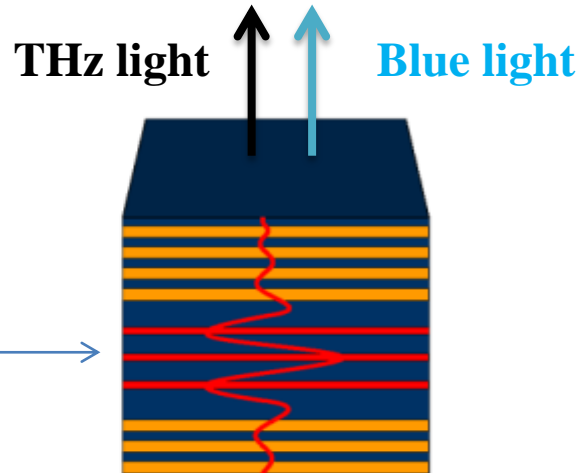
New quantum optical effect: Threshold depends on the statistics of photons of pump!





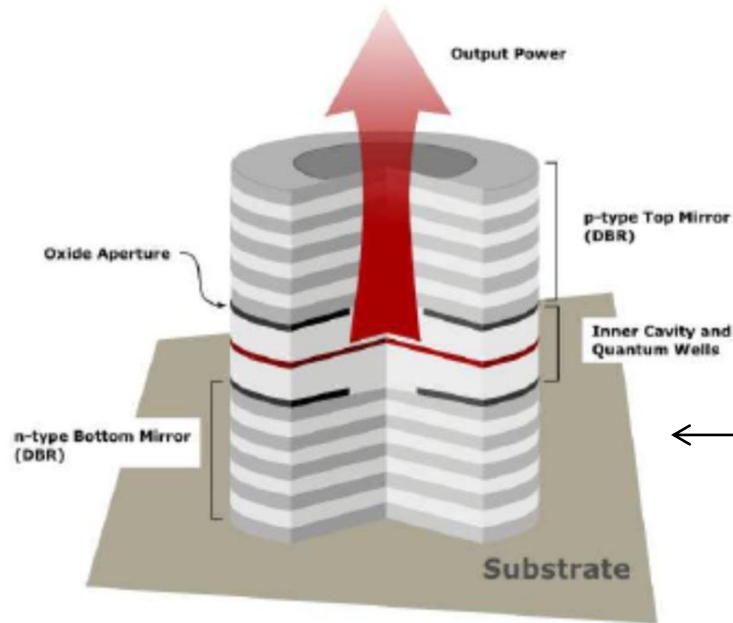
# Schematic of a hybrid GaAs/GaN terahertz polariton laser

GaN based microcavity  
No doping needed!



T=300 K

GaN:  
 $E(2p) = 2\hbar\omega(\text{LED})$



Red Light Emitting Diode based on GaAs



# Conclusions

- Polariton lasers: low threshold coherent light sources, realised in GaAs, CdTe, GaN, ZnO,...
- Two photon pumping of polariton lasers allows building a THz source
- Polariton mediated THz lasers based on GaN: compact, room temperature, vertical geometry, no THz cavity needed
- Hybrid blue light/THz lasers: one can see where to shoot!